CLAIMS

1. A sputtering target containing Ru as a main component, wherein the sputtering target comprises a composite oxide containing boron with a melting point higher than that of B_2O_3, and
wherein the composite oxide is one or more selected from the group consisting of $Co_2B_2O_5$, $CrBO_3$, $TiBO_3$ and $Mn_3B_2O_6$.

2. The sputtering target according to claim 1, wherein the sputtering target has a B content of 0.01 wt% or more.

3. The sputtering target according to claim 1 or 2, wherein the sputtering target has a relative density of 90% or more.

4. The sputtering target according to any one of claims 1 to 3, further comprising one or more selected from Co, Cr, Mn, and Ti as constituent elements, in addition to Ru, B, and O.

5. The sputtering target according to any one of claims 1 to 4, wherein the composite oxide has a melting point of 750 °C or more.

6. A method for manufacturing a sputtering target containing Ru as a main component, the method comprising:
mixing the Ru and a composite oxide having a melting point higher than that of B_2O_3 and containing boron, wherein the composite oxide is one or more selected from the group consisting of $Co_2B_2O_5$, $CrBO_3$, $TiBO_3$ and $Mn_3B_2O_6$.

7. The method according to claim 6, wherein the sputtering target has a B content of 0.01 wt% or more.

8. The method according to claim 6 or 7, wherein the sputtering target has a relative density of 90% or more.

9. The method according to any one of claims 6 to 8, wherein the sputtering target further comprises one or more selected from Co, Cr, Mn, and Ti as constituent elements, in addition to Ru, B, and O.

10. The method according to any one of claims 6 to 9, wherein the composite oxide has a melting point of 750 °C or more.